

N-Channel 200V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
200	0.056 at V _{GS} = 10 V	25
	0.070 at V _{GS} = 6 V	23

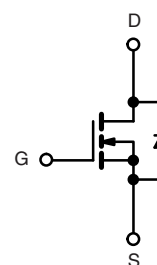
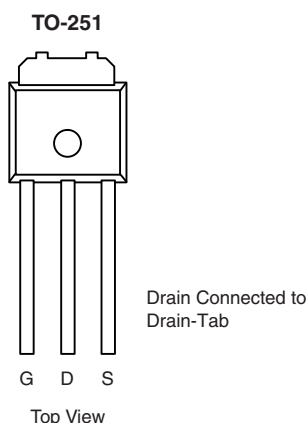
FEATURES

- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Primary Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	200	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	I _D	25	A
	T _C = 125 °C		17	
Pulsed Drain Current		I _{DM}	60	
Continuous Source Current (Diode Conduction)		I _S	19	
Avalanche Current		I _{AS}	25	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	18	mJ
Maximum Power Dissipation	T _C = 25 °C	P _D	145 ^b	W
	T _A = 25 °C		3.5 ^a	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	15	18	°C/W
	Steady State		40	50	
Junction-to-Case (Drain)		R _{thJC}	0.85	1.1	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

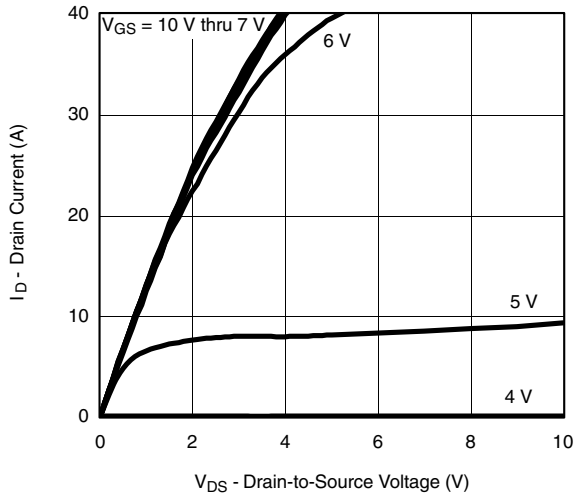
b. See SOA curve for voltage derating.

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	200			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	40			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		0.056		Ω
		$V_{GS} = 10\text{ V}, I_D = 5\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.130		
		$V_{GS} = 10\text{ V}, I_D = 5\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.260		
		$V_{GS} = 6\text{ V}, I_D = 5\text{ A}$		0.070		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 19\text{ A}$		35		S
Dynamic^a						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, F = 1\text{ MHz}$		2400		pF
Output Capacitance	C_{oss}			280		
Reverse Transfer Capacitance	C_{rss}			180		
Total Gate Charge ^c	Q_g	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 19\text{ A}$		40		nC
Gate-Source Charge ^c	Q_{gs}			10		
Gate-Drain Charge ^c	Q_{gd}			15		
Gate Resistance	R_g		0.5		2.9	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 5.2\text{ }\Omega$ $I_D \cong 19\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		15	25	ns
Rise Time ^c	t_r			50	75	
Turn-Off Delay Time ^c	$t_{d(off)}$			30	45	
Fall Time ^c	t_f			60	90	
Source-Drain Diode Ratings and Characteristics ($T_C = 25\text{ }^\circ\text{C}$)						
Pulsed Current	I_{SM}				50	A
Diode Forward Voltage ^b	V_{SD}	$I_F = 19\text{ A}, V_{GS} = 0\text{ V}$		0.9	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 19\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		180	250	ns

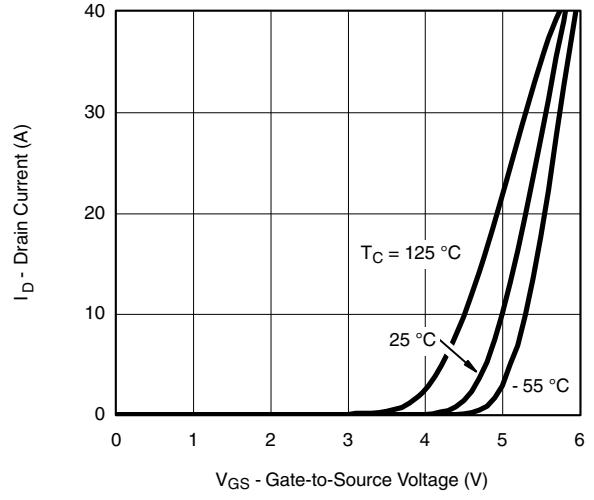
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- c. Independent of operating temperature.

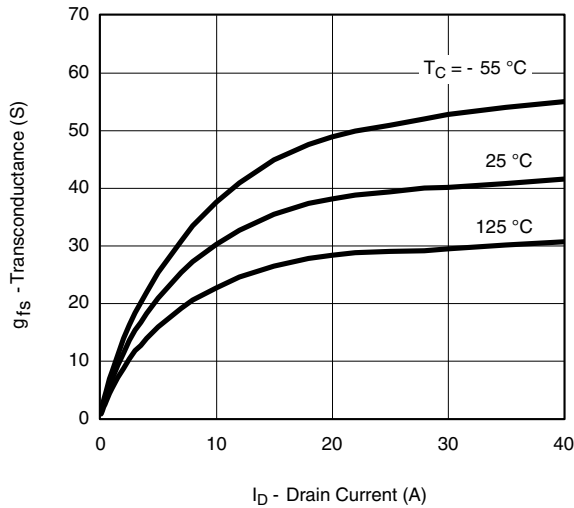
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



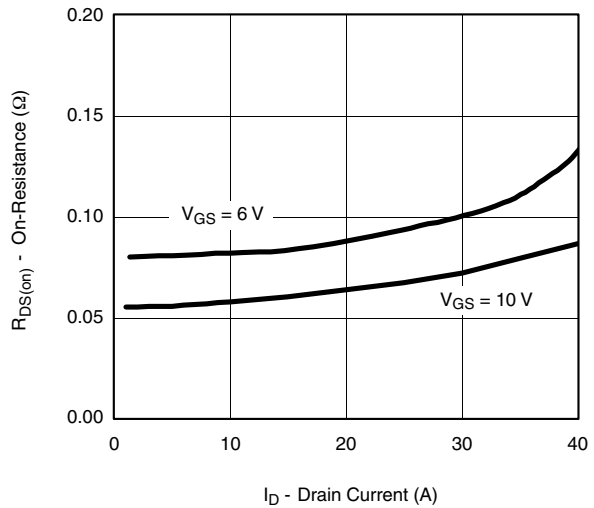
Output Characteristics



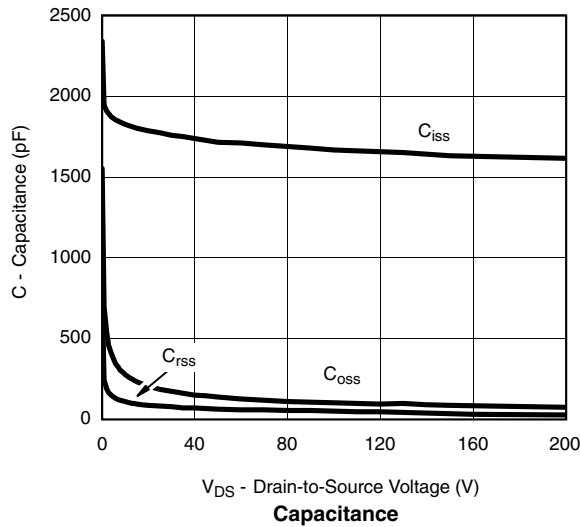
Transfer Characteristics



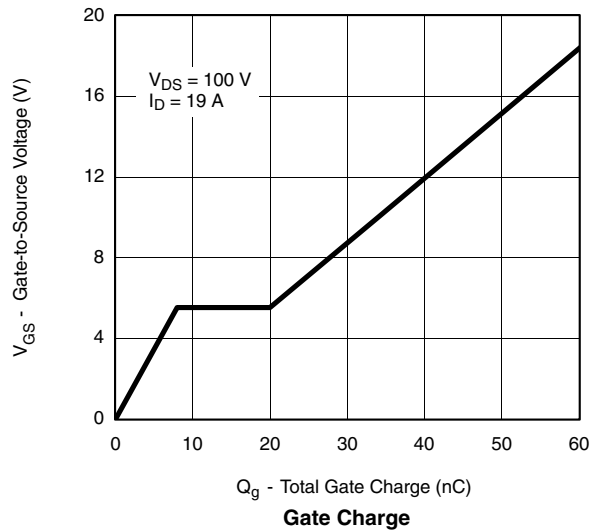
Transconductance



On-Resistance vs. Drain Current

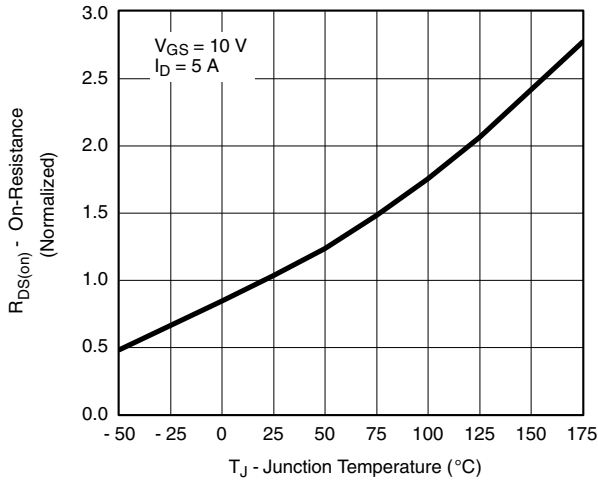


Capacitance

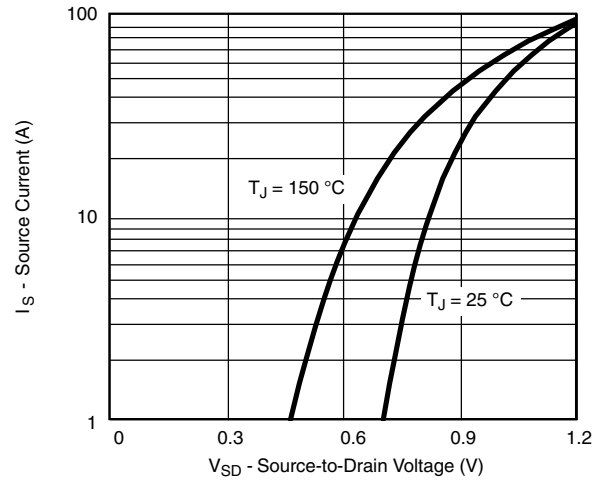


Gate Charge

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

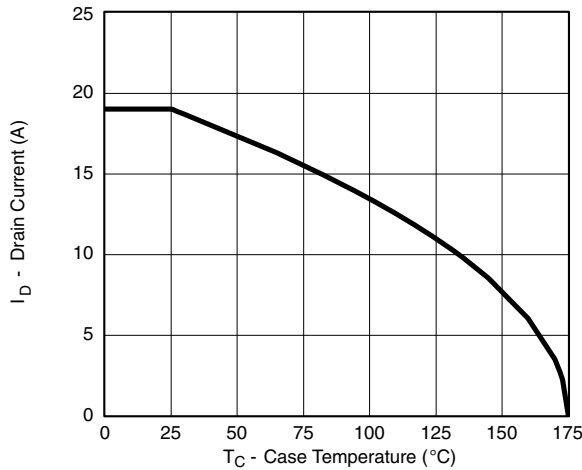


On-Resistance vs. Junction Temperature

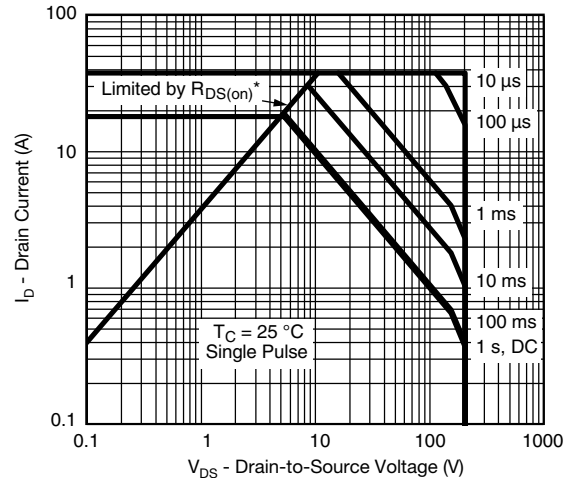


Source-Drain Diode Forward Voltage

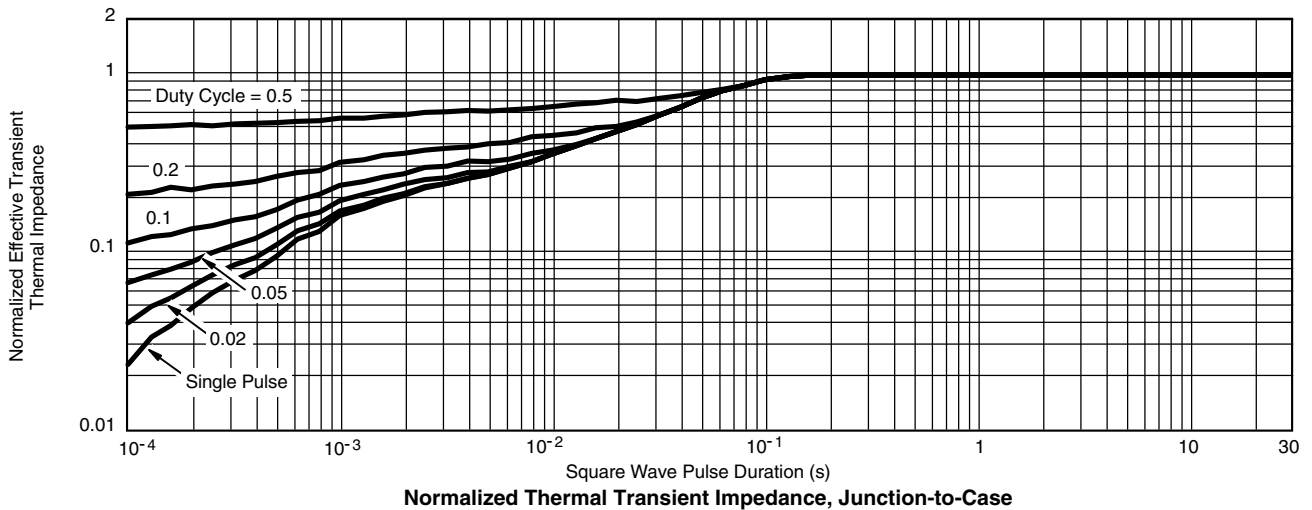
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature

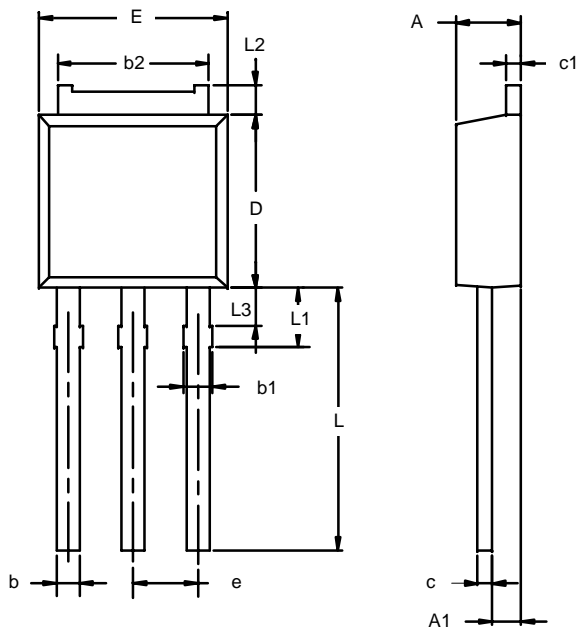


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-251AA



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
E	6.48	6.73	0.255	0.265
e	2.28 BSC		0.090 BSC	
L	3.89	9.53	0.153	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060

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